Hadis Morko

List of Publications by Year in Descending Order

173 papers	6,536 citations	35 h-index	79 g-index
191 ext. papers	7,018 ext. citations	3.4 avg, IF	5.78 L-index

#	Paper	IF	Citations
173	A Platform for Complementary Metal-Oxide-Semiconductor Compatible Plasmonics: High Plasmonic Quality Titanium Nitride Thin Films on Si (001) with a MgO Interlayer. *Advanced Photonics Research*, **2021**, 2, 2000210	1.9	4
172	High-Quality Plasmonic Materials TiN and ZnO:Al by Atomic Layer Deposition. *Physica Status Solidi - Rapid Research Letters*, **2021**, 15, 2100227	2.5	1
171	High-Performance BeMgZnO/ZnO Heterostructure Field-Effect Transistors. *Physica Status Solidi - Rapid Research Letters*, **2020**, 14, 2000371	2.5	1
170	Characterization of Ag Schottky Barriers on Be0.02Mg0.26ZnO/ZnO Heterostructures. *Physica Status Solidi - Rapid Research Letters*, **2018**, 12, 1700366	2.5	7
169	Zinc Oxide Materials and Devices Grown by Molecular Beam Epitaxy **2018**, 343-375		7
168	Polarity Control within One Monolayer at ZnO/GaN Heterointerface: (0001) Plane Inversion Domain Boundary. *ACS Applied Materials & Interfaces*, **2018**, 10, 37651-37660	9.5	3
167	Influence of ZnO thin film crystallinity on biocompatibility. *Toxicology Research*, **2018**, 7, 754-759	2.6	2
166	An alternative material for transparent antennas for commercial and medical applications. *Microwave and Optical Technology Letters*, **2017**, 59, 773-777	1.2	22
165	Recent Development of Boron Nitride towards Electronic Applications. *Advanced Electronic Materials*, **2017**, 3, 1600485	6.4	53
164	Group III Nitrides. *Springer Handbooks*, **2017**, 1-1	1.3	7
163	III-Nitride Light-Emitting Diodes **2017**, 1-21		
162	Status of Growth of Group III-Nitride Heterostructures for Deep Ultraviolet Light-Emitting Diodes. *Crystals*, **2017**, 7, 300	2.3	28
161	Polarity control and residual strain in ZnO epilayers grown by molecular beam epitaxy on (0001) GaN/sapphire. *Physica Status Solidi - Rapid Research Letters*, **2016**, 10, 682-686	2.5	14
160	Improvement of optical quality of semipolar (112□2) GaN on m-plane sapphire by in-situ epitaxial lateral overgrowth. *Journal of Applied Physics*, **2016**, 119, 145303	2.5	10
159	Enhancement of optical and structural quality of semipolar (11-22) GaN by introducing nanoporous SiNxinterlayers **2015**,		2
158	Indium-incorporation efficiency in semipolar (11-22) oriented InGaN-based light emitting diodes **2015**,		5
157	Active region dimensionality and quantum efficiencies of InGaN LEDs from temperature dependent photoluminescence transients **2015**,		3

156	Strong carrier localization in stacking faults in semipolar (11-22) GaN **2015**,		2
155	Modulation-Doped Field-Effect Transistors (MODFET) **2015**, 1-50		1
154	Thickness variations and absence of lateral compositional fluctuations in aberration-corrected STEM images of InGaN LED active regions at low dose. *Microscopy and Microanalysis*, **2014**, 20, 864-8	0.5	9
153	Saga of efficiency degradation at high injection in InGaN light emitting diodes. *Turkish Journal of Physics*, **2014**, 38, 269-313	1.6	11
152	InGaN light-emitting diodes: Efficiency-limiting processes at high injection. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2013**, 31, 050809	2.9	37
151	Carrier Transport **2013**, 115-175		1
150	Field Effect Transistors **2013**, 349-447		
149	Light-Emitting Diodes and Lighting **2013**, 209-266		2
148	Semiconductor Lasers: Light Amplification by Stimulated Emission of Radiation **2013**, 267-348		
147	General Properties of Nitrides **2013**, 1-61		1
146	The p□ Junction **2013**, 177-192		
145	Metal Contacts **2013**, 97-113		
144	Doping: Determination of Impurity and Carrier Concentrations **2013**, 63-95		
143	Optical Processes **2013**, 193-207		
142	Enhanced microwave dielectric tunability of Ba0.5Sr0.5TiO3 thin films grown with reduced strain on DyScO3 substrates by three-step technique. *Journal of Applied Physics*, **2013**, 113, 044108	2.5	12
141	Carrier dynamics in bulk GaN. *Journal of Applied Physics*, **2012**, 111, 023702	2.5	57
140	Carrier dynamics under two- and single-photon excitation in bulk GaN. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 503-506	1.3	2
139	The effect of barrier strain on the reliability of Inx Al1□N/AlN/GaN heterostructure field-effect transistors. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 163-165	2.5	1

138	Growth and Characterization of GaN/ZnO Heteroepitaxy and ZnO-Based Hybrid Devices **2011**, 221-264		1
137	Photoluminescence of Mg-doped m-plane GaN grown by MOCVD on bulk GaN substrates. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1532-1534	1.6	6
136	Measurements of generation-recombination effect by low-frequency phase-noise technique in AlGaN/GaN MOSHFETs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1539-1543		3
135	Reduction of Flicker Noise in AlGaN/GaN-Based HFETs After High Electric-Field Stress. *IEEE Electron Device Letters*, **2011**, 32, 1513-1515	4.4	3
134	Field-assisted emission in AlGaN/GaN heterostructure field-effect transistors using low-frequency noise technique. *Journal of Applied Physics*, **2011**, 109, 084522	2.5	15
133	Ti/Al/Ni/Au Ohmic contacts for AlInN/AlN/GaN-based heterojunction field-effect transistors. *Journal of Applied Physics*, **2010**, 107, 014508	2.5	26
132	Low-Frequency Noise Measurements of AlGaN/GaN Metal□Oxide□Semiconductor Heterostructure Field-Effect Transistors With HfAlO Gate Dielectric. *IEEE Electron Device Letters*, **2010**, 31, 1041-1043	4.4	19
131	ZnO Devices and Applications: A Review of Current Status and Future Prospects. *Proceedings of the IEEE*, **2010**, 98, 1255-1268	14.3	556
130	Bulk ZnO: Current Status, Challenges, and Prospects. *Proceedings of the IEEE*, **2010**, 98, 1339-1350	14.3	35
129	GaN-Based Light-Emitting Diodes: Efficiency at High Injection Levels. *Proceedings of the IEEE*, **2010**, 98, 1180-1196	14.3	84
128	Doping Asymmetry Problem in ZnO: Current Status and Outlook. *Proceedings of the IEEE*, **2010**, 98, 1269-1280	14.3	162
127	Small Signal Equivalent Circuit Modeling for AlGaN/GaN HFET: Hybrid Extraction Method for Determining Circuit Elements of AlGaN/GaN HFET. *Proceedings of the IEEE*, **2010**, 98, 1140-1150	14.3	44
126	Status of Reliability of GaN-Based Heterojunction Field Effect Transistors. *Proceedings of the IEEE*, **2010**, 98, 1127-1139	14.3	28
125	Ferromagnetism in ZnO- and GaN-Based Diluted Magnetic Semiconductors: Achievements and Challenges. *Proceedings of the IEEE*, **2010**, 98, 1288-1301	14.3	23
124	Effect of carrier spillover and Auger recombination on the efficiency droop in InGaN-based blue LEDs. *Superlattices and Microstructures*, **2010**, 47, 118-122	2.8	16
123	Stress test measurements of lattice-matched InAlN/AlN/GaN HFET structures. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1345-1347	1.6	2
122	Microstructure and field mapping of AlInN-based heterostructures and devices. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2436-2439		4
121	Self-Assembled Guanosine-Based Nanoscale Molecular Photonic Devices **2010**, 77-99		

120	Effect of large strain on dielectric and ferroelectric properties of Ba0.5Sr0.5TiO3 thin films. *Applied Physics Letters*, **2009**, 95, 012907	3.4	15
119	Epitaxial growth of (001)-oriented Ba0.5Sr0.5TiO3 thin films on a-plane sapphire with an MgO/ZnO bridge layer. *Applied Physics Letters*, **2009**, 95, 212901	3.4	17
118	ZnO Growth **2009**, 77-129		
117	ZnO Nanostructures **2009**, 365-386		2
116	Optical Properties **2009**, 131-244		3
115	Hot phonons in InAlN/AlN/GaN heterostructure 2DEG channels **2009**,		8
114	On the Light Emission in GaN Based Heterostructures at High Injection. *Materials Research Society Symposia Proceedings*, **2009**, 1202, 23		1
113	ZnO-Based Dilute Magnetic Semiconductors **2009**, 277-350		
112	Processing, Devices, and Heterostructures **2009**, 387-467		
111	Doping of ZnO **2009**, 245-275		4
110	Bandgap Engineering **2009**, 351-364		2
109	General Properties of ZnO **2009**, 1-76		14
108	Microwave ferrites, part 1: fundamental properties. *Journal of Materials Science: Materials in Electronics*, **2009**, 20, 789-834	2.1	280
107	Microwave ferrites, part 2: passive components and electrical tuning. *Journal of Materials Science: Materials in Electronics*, **2009**, 20, 911-952	2.1	95
106	Intrinsic Polarization of Self-Assembled Guanosine Supramolecules in GaN-Based Metal–Semiconductor–Metal Nano-Structures. *Journal of Display Technology*, **2009**, 5, 446-451		2
105	Polarization in GaN Based Heterostructures and Heterojunction Field Effect Transistors (HFETs) **2008**, 373-466		2
104	Large pyroelectric effect in undoped epitaxial Pb(Zr,Ti)O3 thin films on SrTiO3 substrates. *Applied Physics Letters*, **2008**, 93, 052913	3.4	24
103	On the efficiency droop in InGaN multiple quantum well blue light emitting diodes and its reduction with p-doped quantum well barriers. *Applied Physics Letters*, **2008**, 93, 121107	3.4	275

102	Reduction of efficiency droop in InGaN light emitting diodes by coupled quantum wells. *Applied Physics Letters*, **2008**, 93, 171113	3.4	181
101	Studies of III-Nitride Superlattice Structures Implanted with Lanthanide Ions. *Materials Research Society Symposia Proceedings*, **2008**, 1111, 1		3
100	Large electro-optic effect in single-crystal Pb(Zr,Ti)O3 (001) measured by spectroscopic ellipsometry. *Journal of Applied Physics*, **2008**, 104, 093103	2.5	16
99	High-□ielectrics and advanced channel concepts for Si MOSFET. *Journal of Materials Science: Materials in Electronics*, **2008**, 19, 915-951	2.1	61
98	Defect reduction in GaN epilayers grown by metal-organic chemical vapor deposition with in situ SiNx nanonetwork. *Applied Physics Letters*, **2007**, 90, 262112	3.4	20
97	Comparative Study of Thin PZT Sol-gel Films Deposited on Pt and GaN Substrates. *Materials Research Society Symposia Proceedings*, **2007**, 1034, 152		
96	Structural and electrical properties of Pb(Zr,Ti)O3 grown on (0001) GaN using a double PbTiO3□PbO bridge layer. *Applied Physics Letters*, **2007**, 91, 182908	3.4	27
95	Epitaxial growth of ZrO2 on GaN templates by oxide molecular beam epitaxy. *Applied Physics Letters*, **2007**, 91, 022916	3.4	3
94	A General Nonlithographic Method for Producing Nanodots by RIE Etching. *Materials Research Society Symposia Proceedings*, **2007**, 1059, 1		
93	Hydrostatic Pressure Studies of GaN/AlGaN/GaN Heterostructure Devices with Varying AlGaN Thickness and Composition. *Materials Research Society Symposia Proceedings*, **2007**, 994, 1		
92	Effect of Growth Conditions on Defect-related Photoluminescence in ZnO Thin Films Grown by Plasma Assisted MBE. *Materials Research Society Symposia Proceedings*, **2007**, 1035, 1		
91	Blue and Yellow Luminescence in ZnO Films Grown by Peroxide MBE. *Materials Research Society Symposia Proceedings*, **2007**, 1035, 1		
90	Photoelectrochemical Etching of GaN Thin Films With Varying Carrier Concentrations. *Materials Research Society Symposia Proceedings*, **2007**, 1040, 1		
89	High electron mobility in nearly lattice-matched AlInN□AlN□GaN heterostructure field effect transistors. *Applied Physics Letters*, **2007**, 91, 132116	3.4	91
88	Electrical Characterization of Isotype n-ZnO/n-GaN Heterostructures. *Materials Research Society Symposia Proceedings*, **2006**, 957, 1		
87	Investigation of Epitaxially Grown PbO, TiO2 and ZrO2 as Bridge Layers for Integration of PZT on GaN by MBE. *Materials Research Society Symposia Proceedings*, **2006**, 966, 1		1
86	Persistent Photoconductivity in High-mobility AlxGa1□N/AlN/GaN Heterostructures Grown by Metal-organic Vapor-phase Epitaxy. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
85	Transport Properties and Conduction Band Offset of n-ZnO/n-6H-SiC Heterostructures. *Materials Research Society Symposia Proceedings*, **2006**, 957, 1		

84	Schottky I-V Characteristics of Au/Ni/GaN/SiNx nanonework/sapphire structures. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
83	1.37 - 2.90 Micron Intersubband Transitions in GaN/AlN Superlattices. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
82	Structural and Optical Properties of PbTiO3 Grown on SrTiO3 Substrates by Peroxide MBE. *Materials Research Society Symposia Proceedings*, **2006**, 966, 1		4
81	Growth of High-Quality Pb(ZrxTi1-x)O3 Films by Peroxide MBE and Their Optical and Structural Characteristics. *Materials Research Society Symposia Proceedings*, **2006**, 966, 1		2
80	Effects of Rapid Thermal Annealing Treatment on the Surface Band Bending of n-type GaN Studied by Surface Potential Electric Force Microscopy. *Materials Science Forum*, **2006**, 527-529, 1529-1532	0.4	2
79	High quality epitaxial growth of PbTiO3 by molecular beam epitaxy using H2O2 as the oxygen source. *Applied Physics Letters*, **2006**, 89, 122912	3.4	18
78	Fabrication and current-voltage characterization of a ferroelectric lead zirconate titanate/AlGaN□GaN field effect transistor. *Applied Physics Letters*, **2006**, 88, 123508	3.4	36
77	I-V characteristics of Au□Ni Schottky diodes on GaN with SiNx nanonetwork. *Applied Physics Letters*, **2006**, 89, 152108	3.4	14
76	Epitaxial Growth of ZrO2 on GaN by MOMBE for High Dielectric Material Applications. *Materials Research Society Symposia Proceedings*, **2006**, 955, 1		
75	III-V Nitrides and Silicon Carbide as Optoelectronic Materials **2006**, 4-1-4-59		
74	GaN-Based Modulation-Doped FETs and Heterojunction Bipolar Transistors **2006**, 547-626		1
73	Near-infrared wavelength intersubband transitions in GaN□AlN short period superlattices. *Applied Physics Letters*, **2006**, 89, 151112	3.4	12
72	Group III Nitrides **2006**, 753-804		3
71	Luminescence properties of defects in GaN. *Journal of Applied Physics*, **2005**, 97, 061301	2.5	1461
70	Visible-ultraviolet spectroscopic ellipsometry of lead zirconate titanate thin films. *Applied Physics Letters*, **2005**, 86, 262902	3.4	15
69	Dielectric functions and electronic band structure of lead zirconate titanate thin films. *Journal of Applied Physics*, **2005**, 98, 094108	2.5	59
68	Resonant surface plasmon-induced modification of photoluminescence from GaN/AlN quantum dots. *Nanotechnology*, **2004**, 15, 1252-1255	3.4	24
67	Surface band bending in as-grown and plasma-treated n-type GaN films using surface potential electric force microscopy. *Applied Physics Letters*, **2004**, 84, 3070-3072	3.4	39

66	GaN epitaxy on thermally treated c-plane bulk ZnO substrates with O and Zn faces. *Applied Physics Letters*, **2004**, 84, 2268-2270	3.4	57
65	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. *Materials Research Society Symposia Proceedings*, **2003**, 799, 257		
64	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. *Materials Research Society Symposia Proceedings*, **2003**, 789, 334		
63	Growth Structure, and Optical Properties of III-Nitride Quantum Dots. *Materials Research Society Symposia Proceedings*, **2003**, 794, 177		
62	Epitaxy of highly optical efficient GaN on O and Zn face ZnO. *Materials Research Society Symposia Proceedings*, **2003**, 798, 748		
61	Generation□ecombination noise in gallium nitride-based quantum well structures. *Journal of Applied Physics*, **2003**, 93, 5337-5345	2.5	8
60	Infrared optical absorbance of intersubband transitions in GaN/AlGaN multiple quantum well structures. *Journal of Applied Physics*, **2003**, 93, 10140-10142	2.5	14
59	Stimulated emission and ultrafast carrier relaxation in AlGaN/GaN multiple quantum wells. *Applied Physics Letters*, **2003**, 82, 4080-4082	3.4	11
58	GROWTH OF III-NITRIDE SEMICONDUCTORS AND THEIR CHARACTERIZATION **2003**, 1-124		
57	Bowing Parameter of AlxGa1-xN. *Materials Research Society Symposia Proceedings*, **2002**, 722, 321		
56	GaN-based modulation doped FETs and UV detectors. *Solid-State Electronics*, **2002**, 46, 157-202	1.7	137
55	GROWTH, STRUCTURES, AND OPTICAL PROPERTIES OF III-NITRIDE QUANTUM DOTS. *International Journal of High Speed Electronics and Systems*, **2002**, 12, 79-110	0.5	18
54	Energy band bowing parameter in AlxGa1□N alloys. *Journal of Applied Physics*, **2002**, 92, 4837-4839	2.5	108
53	III-Nitride semiconductor growth by MBE: Recent issues. *Journal of Materials Science: Materials in Electronics*, **2001**, 12, 677-695	2.1	29
52	Systematic measurement of AlxGa1□N refractive indices. *Applied Physics Letters*, **2001**, 79, 4103-4105	3.4	65
51	Investigation of Buffer Layers for GaN Grown by MBE. *Materials Research Society Symposia Proceedings*, **2000**, 639, 3171		
50	POLARIZATION EFFECTS IN NITRIDE SEMICONDUCTOR HETEROSTRUCTURES. *International Journal of High Speed Electronics and Systems*, **2000**, 10, 25-37	0.5	6
49	Photoreflectance investigations of the bowing parameter in AlGaN alloys lattice-matched to GaN. *Applied Physics Letters*, **1999**, 74, 3353-3355	3.4	43

48	Polarization effects in nitride semiconductor device structures and performance of modulation doped field effect transistors. *Solid-State Electronics*, **1999**, 43, 1909-1927	1.7	92
47	Microcalorimetric absorption spectroscopy in GaN□AlGaN quantum wells. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 59, 319-322	3.1	
46	Polarization effects in nitride semiconductors and device structures. *Materials Research Innovations*, **1999**, 3, 97-106	1.9	16
45	Optical Processes in Nitride Semiconductors. *Springer Series in Materials Science*, **1999**, 295-339	0.9	
44	Metal Contacts to GaN. *Springer Series in Materials Science*, **1999**, 191-215	0.9	
43	Electronic Band Structure of Bulk and QW Nitrides. *Springer Series in Materials Science*, **1999**, 45-82	0.9	1
42	Recombination dynamics of free and localized excitons in GaN/Ga0.93Al0.07N quantum wells. *Physical Review B*, **1998**, 57, R9447-R9450	3.3	103
41	In situ transmission electron microscopy of AlN growth by nitridation of (0001) □Al2O3. *Journal of Applied Physics*, **1998**, 83, 2847-2850	2.5	34
40	Megahertz bandwidth AlxGa1-xN/GaN-based p-i-n detectors **1998**, 3287, 198		4
39	Metal□nsulator□emiconductor structure on GaAs using a pseudomorphic Si/GaP interlayer. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1997**, 15, 252		4
38	On the inversion in GaAs metal-insulator-semiconductor heterostructures. *Applied Physics Letters*, **1997**, 70, 228-230	3.4	2
37	Minority-carrier characteristics of SiNx/GaAs metal□nsulator□emiconductor structures with Si/Ge interlayers. *Applied Physics Letters*, **1997**, 71, 1210-1212	3.4	12
36	Proposed explanation of the anomalous doping characteristics of III□V nitrides. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1997**, 76, 131-143		12
35	Si3N4/Si/In0.05Ga0.95As/n□GaAs metal□nsulator□emiconductor devices. *Journal of Applied Physics*, **1997**, 81, 516-523	2.5	6
34	Characteristics of Si3N4/GaAs metal-lnsulator-semiconductor interfaces with coherent Si/Al0.3Ga0.7As interlayers. *Journal of Electronic Materials*, **1997**, 26, 1076-1082	1.9	2
33	Very low resistance multilayer Ohmic contact to n-GaN. *Applied Physics Letters*, **1996**, 68, 1672-1674	3.4	390
32	Oscillator strengths for optical band-to-band processes in GaN epilayers. *Physical Review B*, **1996**, 54, 7678-7681	3.3	76
31	Metal-insulator-semiconductor structures on p-type GaAs with low interface state density. *Applied Physics Letters*, **1996**, 69, 230-232	3.4	35

30	Theoretical investigation of electrical characteristics of AlGaN/GaN modulation doped field-effect transistors. *Journal of Applied Physics*, **1996**, 80, 3031-3042	2.5	63
29	Photoluminescence characterization of the quantum well structure and influence of optical illumination on the electrical performance of AlGaN/GaN modulation-doped field-effect transistors. *Applied Physics Letters*, **1996**, 69, 1420-1422	3.4	53
28	Characteristics of Si3N4/Si/n-GaAs metal-insulator-semiconductor interfaces grown on GaAs(111)B substrate. *Applied Physics Letters*, **1996**, 69, 3025-3027	3.4	8
27	Suppression of leakage currents and their effect on the electrical performance of AlGaN/GaN modulation doped field-effect transistors. *Applied Physics Letters*, **1996**, 69, 1229-1231	3.4	45
26	Interface properties of Si3N4Si/n-GaAs metal-msulator-semiconductor structure using a Si interlayer. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1996**, 74, 219-234		12
25	Electrical conduction in silicon nitrides deposited by plasma enhanced chemical vapour deposition. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1996**, 73, 723-736		48
24	LATTICE-MISMATCHED HETEROEPITAXY **1995**, 145-209		
23	Properties of GaAs on Si grown by molecular beam epitaxy. *Critical Reviews in Solid State and Materials Sciences*, **1990**, 16, 91-114	10.1	26
22	Cathodoluminescence measurement of an orientation dependent aluminum concentration in AlxGa1−xAs epilayers grown by molecular beam epitaxy on a nonplanar substrate. *Applied Physics Letters*, **1989**, 54, 1347-1349	3.4	31
21	Experimental study of the frequency limits of a resonant tunneling oscillator. *Applied Physics Letters*, **1986**, 48, 422-424	3.4	25
20	Measurement of the minority-carrier lifetime and injection efficiency in AlGaAs/GaAs heterojunction bipolar transistors. *Applied Physics Letters*, **1986**, 48, 367-369	3.4	5
19	A pnp AlGaAs/GaAs heterojunction bipolar transistor. *Applied Physics Letters*, **1985**, 46, 302-304	3.4	13
18	Collector-emitter offset voltage in AlGaAs/GaAs heterojunction bipolar transistors. *Applied Physics Letters*, **1985**, 47, 313-315	3.4	83
17	New high-speed (Al, Ga) as modulation doped field-effect transistors. *IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems*, **1985**, 1, 35-38		0
16	Modulation Doped A1xGa1-xAs/GaAs Field Effect Transistors (MODFETS): Analysis, Fabrication and Performance **1985**, 625-676		5
15	Temperature dependence of current gain in AlGaAs/GaAs heterojunction bipolar transistors. *Applied Physics Letters*, **1984**, 45, 1086-1088	3.4	23
14	Comprehensive analysis of Si-doped AlxGa1−xAs (x=0 to 1): Theory and experiments. *Physical Review B*, **1984**, 30, 4481-4492	3.3	373
13	Electron density of the two-dimensional electron gas in modulation doped layers. *Journal of Applied Physics*, **1983**, 54, 2093-2096	2.5	111

12	Transport properties of Sn-doped AlxGa1−xAs grown by molecular beam epitaxy. *Journal of Applied Physics*, **1980**, 51, 4882-4884	2.5	39
11	Chromium and tellurium redistribution in GaAs and Al0.3Ga0.7As grown by molecular beam epitaxy. *Journal of Applied Physics*, **1980**, 51, 5986-5991	2.5	20
10	High-purity GaAs and Cr-doped GaAs epitaxial layers by MBE. *Journal of Applied Physics*, **1979**, 50, 6413-6416	2.5	53
9	Purity of GaAs grown by LPE in a graphite boat. *Journal of Crystal Growth*, **1976**, 36, 109-114	1.6	27
8	The Growth of Uniform Submicron GaAs Layers by Liquid Phase Epitaxy. *Journal of the Electrochemical Society*, **1976**, 123, 906-912	3.9	9
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